

P-Channel 60 V (D-S) 175 °C MOSFET

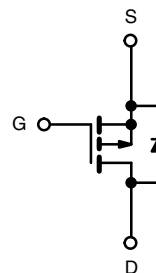
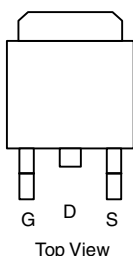
PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
- 60	0.019 at $V_{GS} = - 10$ V	- 55	76
	0.025 at $V_{GS} = - 4.5$ V	- 48	

FEATURES

- TrenchFET[®] Power MOSFET
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

TO-263


P-Channel MOSFET

Ordering Information: SUM55P06-19L-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^d ($T_J = 175$ °C)	I_D	$T_C = 25$ °C - 55	A
		$T_C = 125$ °C - 31	
Pulsed Drain Current	I_{DM}	- 150	
Avalanche Current	I_{AS}	- 45	
Single Pulse Avalanche Energy ^a	E_{AS}	101	mJ
Power Dissipation	P_D	$T_C = 25$ °C 125 ^c	W
		$T_A = 25$ °C ^b 3.75	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case	R_{thJC}	1.2	

Notes:

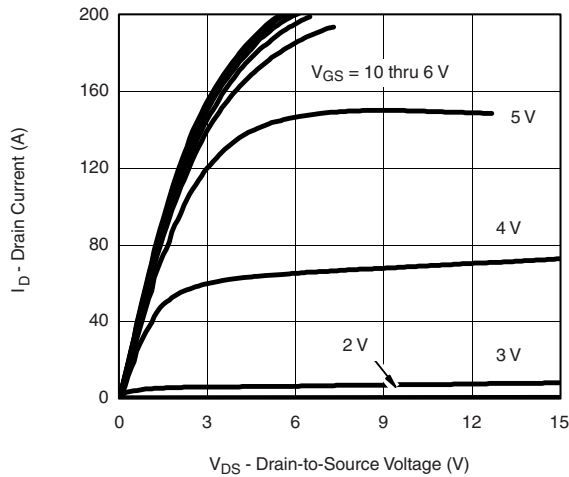
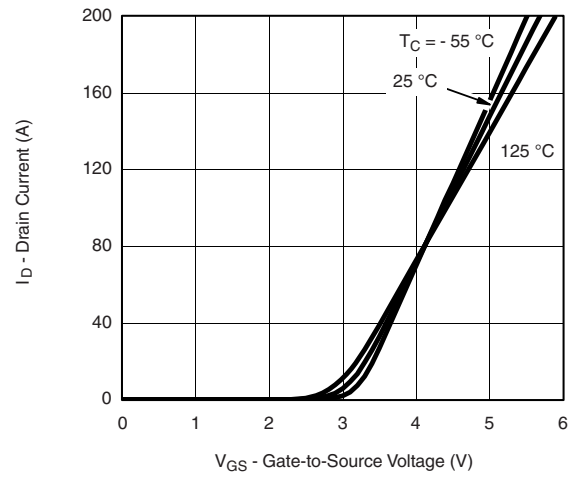
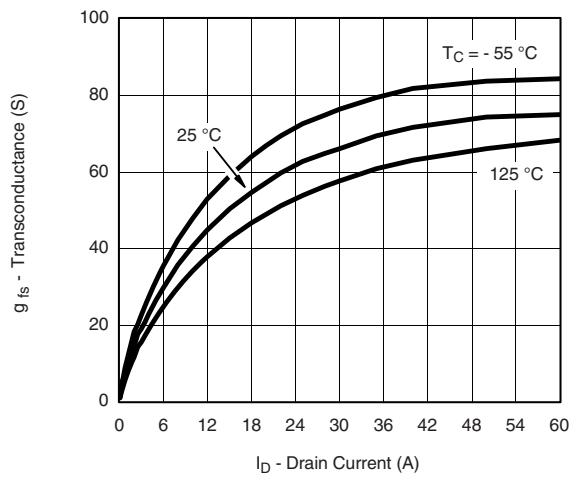
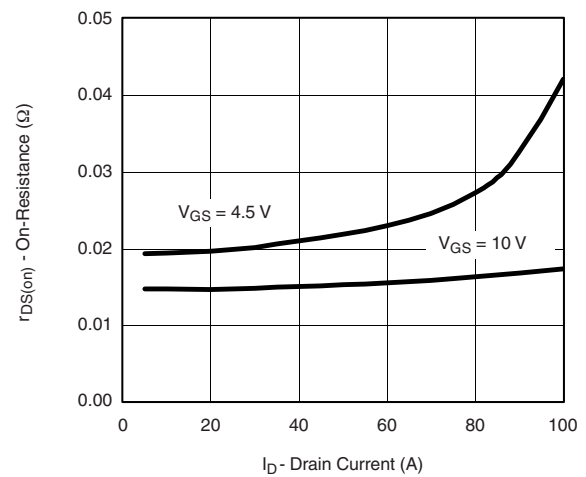
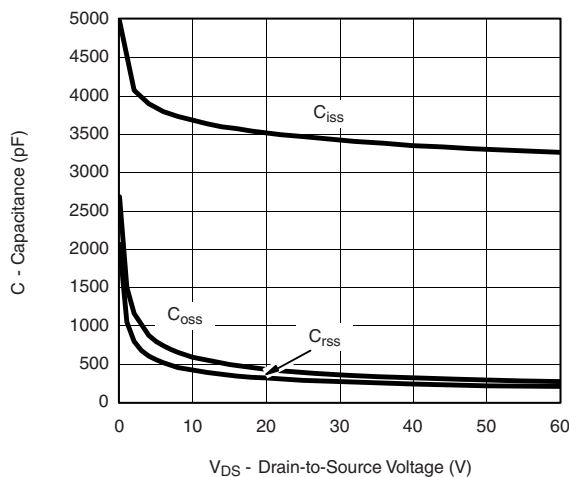
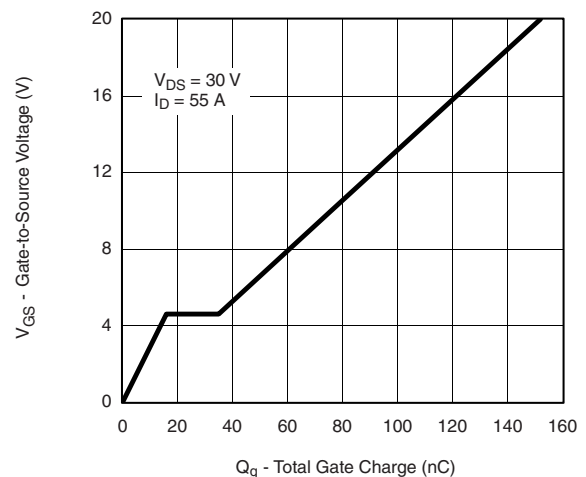
- Duty cycle $\leq 1\%$.
- When mounted on 1" square PCB (FR-4 material).
- See SOA curve for voltage derating.
- Limited by package.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 175 °C			- 250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 120			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 30 A		0.015	0.019	Ω
		V _{GS} = - 10 V, I _D = - 30 A, T _J = 125 °C			0.033	
		V _{GS} = - 10 V, I _D = - 30 A, T _J = 175 °C			0.041	
		V _{GS} = - 4.5 V, I _D = - 20 A		0.020	0.025	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 50 A	20			S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1 MHz		3500		pF
Output Capacitance	C _{oss}			390		
Reverse Transfer Capacitance	C _{rss}			290		
Total Gate Charge ^c	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 55 A		76	115	nC
Gate-Source Charge ^c	Q _{gs}			16		
Gate-Drain Charge ^c	Q _{gd}			19		
Gate Resistance	R _g	f = 1 MHz		5.2		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 30 V, R _L = 0.54 Ω I _D ≡ - 55 A, V _{GEN} = - 10 V, R _g = 2.5 Ω		12	20	ns
Rise Time ^c	t _r			15	25	
Turn-Off Delay Time ^c	t _{d(off)}			80	120	
Fall Time ^c	t _f			230	350	
Source-Drain Diode Ratings and Characteristics T _C = 25 °C ^b						
Continuous Current	I _S				- 110	A
Pulsed Current	I _{SM}				- 240	
Forward Voltage ^a	V _{SD}	I _F = - 50 A, V _{GS} = 0 V		- 1	- 1.5	V
Reverse Recovery Time	t _{rr}	I _F = - 50 A, di/dt = 100 A/μs		45	68	ns
Peak Reverse Recovery Current	I _{RM(REC)}			- 2.6	- 4	A
Reverse Recovery Charge	Q _{rr}				0.059	0.136

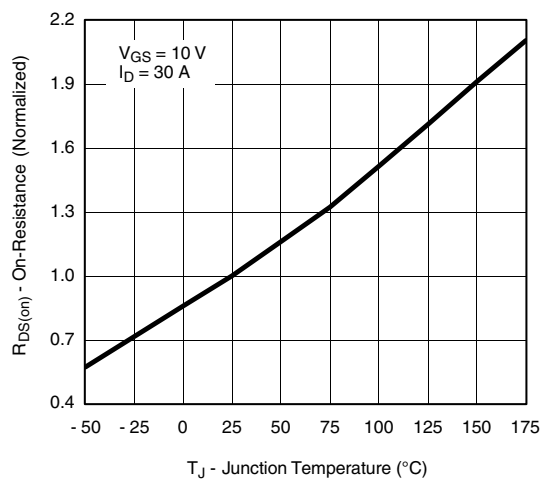
Notes:

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

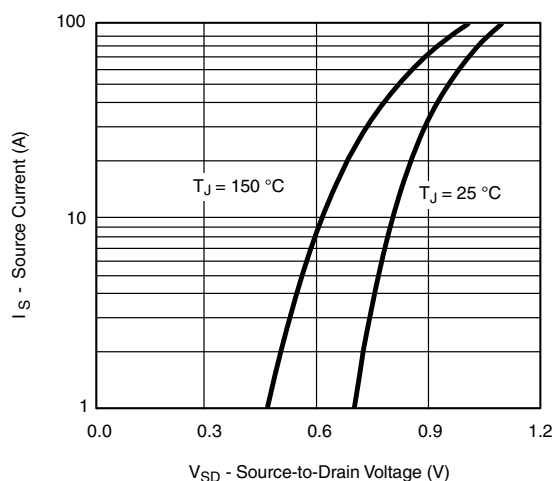
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

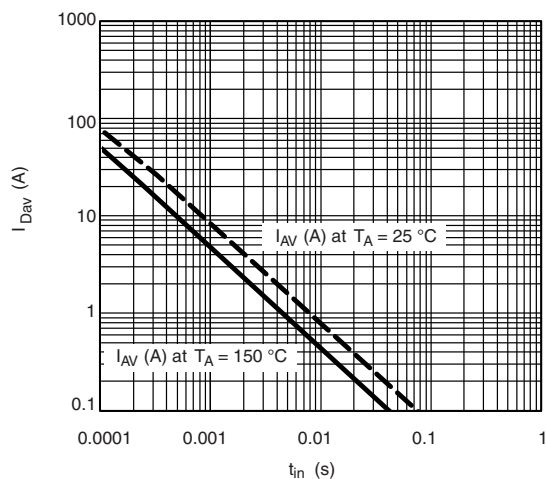
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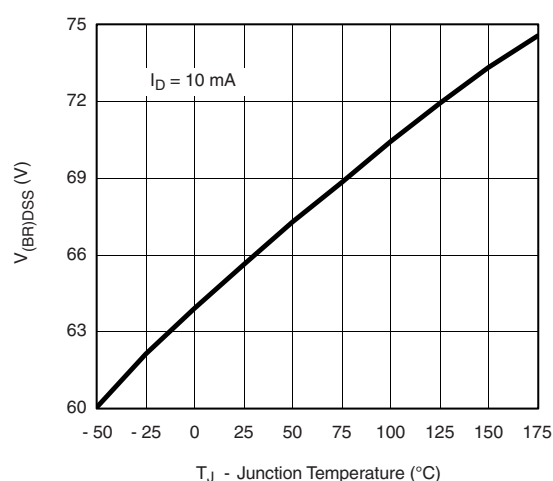
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

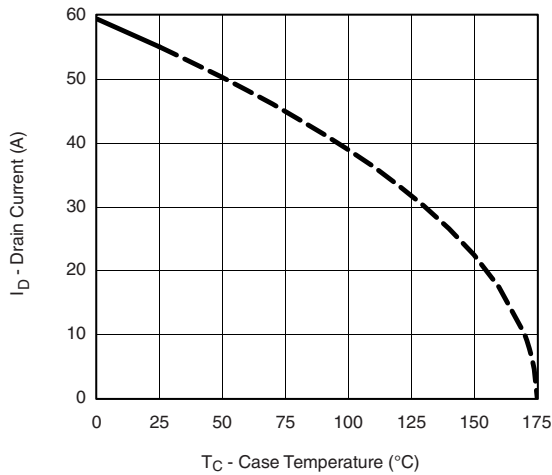


Avalanche Current vs. Time

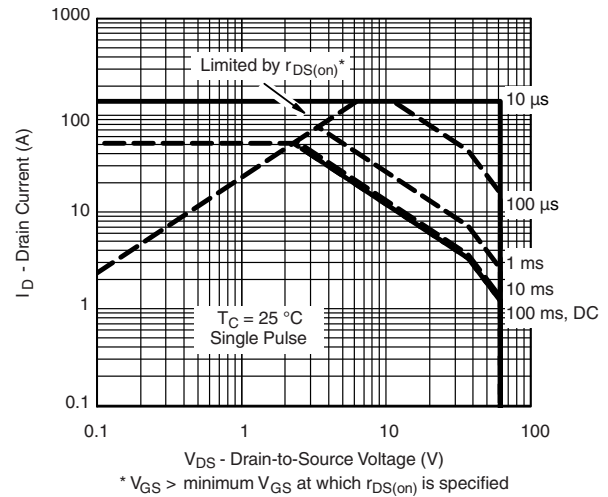


Drain Source Breakdown vs. Junction Temperature

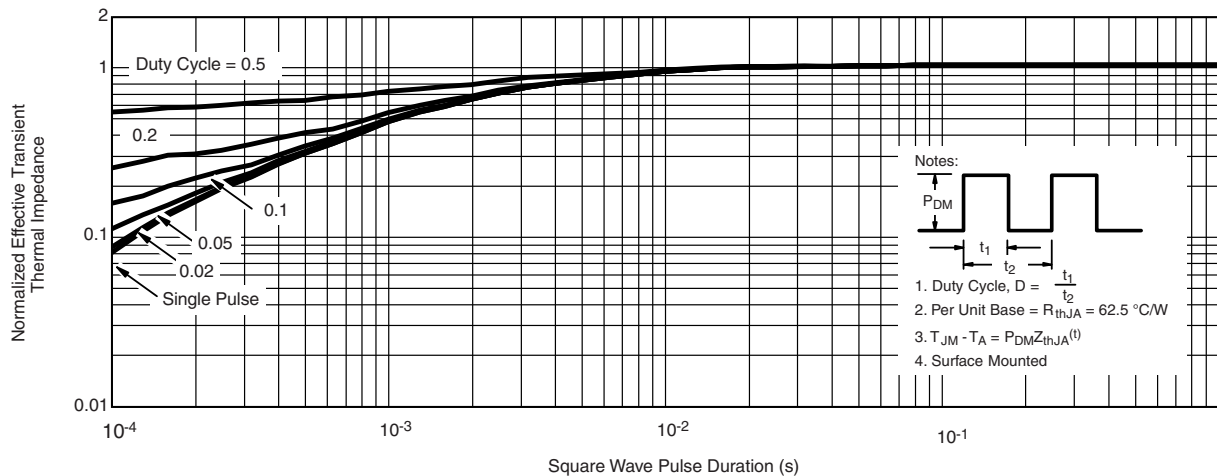
THERMAL RATINGS



Maximum Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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